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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/674,925	11/08/2000	Jyoti Kiron Bhardwaj	WLJ.067	7580	
	7590 02/21/2007 FRANCOS, & WHITT PI	LC	EXAM	INER	
ONE FREEDOM SQUARE			AHMED, SHAMIM		
11951 FREEDOM DRIVE SUITE 1260 RESTON, VA 20190			ART UNIT	PAPER NUMBER	
1001011, 1111			1765		
SHORTENED STATUTOR	Y PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE		
3 MOI	NTHS	02/21/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

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,	Application No.	Applicant(s)	
	09/674,925	BHARDWAJ ET AL.	
Office Action Summary	Examiner	Art Unit	
·	Shamim Ahmed	1765	
The MAILING DATE of this communication ap Period for Reply	ppears on the cover sheet w	ith the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING IT Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period. Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mailinearned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNI .136(a). In no event, however, may a d will apply and will expire SIX (6) MOI tte, cause the application to become A	CATION. reply be timely filed ITHS from the mailing date of this communication BANDONED (35 U.S.C. § 133).	
Status			
1)⊠ Responsive to communication(s) filed on 17_	November 2006.		
2a) This action is FINAL . 2b) ☐ Th	is action is non-final.		
3) Since this application is in condition for allow	ance except for formal mat	ters, prosecution as to the merits is	;
closed in accordance with the practice under	Ex parte Quayle, 1935 C.[D. 11, 453 O.G. 213.	
Disposition of Claims			
4)⊠ Claim(s) <u>1,2,4-35 and 38</u> is/are pending in th	e application.		
4a) Of the above claim(s) is/are withdr			
5)⊠ Claim(s) <u>31 and 32</u> is/are allowed.			•
6)⊠ Claim(s) <u>1,2,4-30,33-35 and 38</u> is/are rejecte	d.	•	
7) Claim(s) is/are objected to.		•	
8) Claim(s) are subject to restriction and	or election requirement.		
Application Papers			
9)☐ The specification is objected to by the Examir	ner.		
10) The drawing(s) filed on is/are: a) ac	cepted or b) objected to	by the Examiner.	•
Applicant may not request that any objection to th	e drawing(s) be held in abeya	nce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the corre			d)
11) The oath or declaration is objected to by the I	examiner. Note the attache	d Office Action or form P1O-152.	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreig a) All b) Some * c) None of:	n priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
 Certified copies of the priority docume 	nts have been received.		
2. Certified copies of the priority docume			
3. Copies of the certified copies of the pri	•	received in this National Stage	
application from the International Bure	, , , , , , , , , , , , , , , , , , , ,		
* See the attached detailed Office action for a lis	st of the certified copies no	received.	
Attachment(s)	·	O	
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		Summary (PTO-413) (s)/Mail Date	
3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date		Informal Patent Application	

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DETAILED ACTION

Response to Arguments

1. Applicant's arguments/declaration with respect to the pending claims have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 3. Claims 1-2,4-10,13-18, 33-35 and 38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kawasaki et al (4,795,529) in view of Robaato et al (JP 03-224226 A).

Kawasaki et al disclose an apparatus and a process, wherein etching step and deposition step can be carried out alternately.

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Kawasaki et al also teach that the two alternating steps have different processing parameters such as the voltage is different in the two alternating steps (col.1, lines 66-68, col.2, lines 1-2, and lines 12-17).

Kawasaki et al, further disclose that the plasma generation for the two steps are stabilized by a matching box, that consists of capacitor (col.3, lines 53-65 and col.16, lines 19-21).

Kawasaki et al remain silent about the step of compensating for a mismatch between the impedance of power supply and the impedance of plasma to stabilize the plasma.

However, in a method of plasma generation, Robaato et al teach that an impedance matching network for plasma generating apparatus, that is equipped with a feedback mechanism consisting of an impedance matching circuit and the like and compensating for an impedance mismatch by adjusting or changing at least one feedback parameter such as a microwave power or the like and thereby establishing a substantially constant plasma state (see abstract and constitution page).

Therefore, it would have been obvious to one skilled in the art at the time of claimed invention to combine Robaato et al's teaching into Kawasaki et al's process for establishing a stable plasma by inhibiting fluctuation in the plasma impedance as taught by Robatto et al.

As to claim 4, Kawasaki et al teach that the RF power is inductively coupled into the plasma (see figure 1).

As to claims 6-7, Kawasaki et al teach that the matching box is controlled by electrically such as a controller (col. 7, lines 6-20, col.15, lines 28-32).

As to claims 14-15, Kawasaki inherently teach that the capacitors are adjusted to different values for each of the steps because the matching box or matching unit is adapted to control the RF power source.

As to claims 17 and 18, Kawasaki teaches that the positions of the capacitor do not vary between etch and deposition step (figure 16).

4. Claims 1-2,4-5, 19-25,29-30 and 33-35 rejected under 35 U.S.C. 103(a) as being unpatentable over Okudaira et al (4,985,114) in view of Robaato et al (JP-03224226A).

Okudaira et al disclose a process, wherein etching and deposition is performed alternately into a reaction chamber at predetermined time intervals.

Okudaira et al also disclose that at least etching gas and the deposition gas are supplied alternately and for a certain period of time etching gas and deposition gas can be supplied simultaneously and continuously (col.2, lines 41-49 and figures 1 and 3).

Okudaira et al, further disclose that the intensity of the power is controlled by an impendence matching circuit for compensating the high frequency power supply (col.5, lines 15-17).

Okudaira et al remain silent about the step of compensating for a mismatch between the impedance of power supply and the impedance of plasma to stabilize the plasma.

However, in a method of plasma generation, Robasto et al teach that an impedance matching network for plasma generating apparatus, that is equipped with a feedback mechanism consisting of an impedance matching circuit and the like and compensating for an impedance mismatch by adjusting or changing at least one feedback parameter such as a microwave power or the like and thereby establishing a substantially constant plasma state (see abstract and constitution page).

Therefore, it would have been obvious to one skilled in the art at the time of claimed invention to combine Robaato et al's teaching into Okudaira et al's process for establishing a stable plasma by inhibiting fluctuation in the plasma impedance as taught by Robatto et al.

As to claim 19, Okudaira et al teach that the plasma is stabilized by maintaining a reduced pressure of the alternating etching and depositing gas (col.5, lines 38-42).

As to claim 20, Okudaira et al teach that deposition gas is supplied before the etching gas is switched off or vise- versa (see figure 3).

As to claims 29 and 30, Okudaira et al teach that the pressure is monitored and adjusting the flow of the process gases into the chamber during the alternating etch and deposition steps (col.5, lines 38-42).

5. Claims 11-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kawasaki et al (4,795,529) in view of Robaato et al (JP-03224226A) as applied to claims 1-2,4-10,13-18,33-35 and 38 above, and further in view of Sadinsky (5,424,691).

Kawasaki discloses above in paragraph 3-but fails to disclose that a motor, which is driven by control signals, drives the matching unit.

However, Sadinsky discloses a method, wherein RF power is adapted through an impedance matching net work, that comprises capacitors and are driven by motor for proper adjustment and further more the motor is driven by a signal generator (col.3, lines 28-34 and lines 60-col.4, lines 5).

Therefore, it would have been obvious to one skilled in the art at the time of claimed invention to employ Sadinsky's teaching into modified Kawasaki et al's method for proper adjustment of the capacitors in the matching unit as taught by Sadinsky.

6. Claims 26-28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kawasaki et al (4,795,529) in view of Robaato et al (JP 03-224226 A) as applied to claims 1-2,4-10,13-18, 33-35 and 38 above, and further in view of Leiphart (5882,488).

Kawasaki discloses above in paragraph 3 but fails to disclose that a further gas can be introduced into the chamber to stabilize the plasma.

However, Leiphart teaches that the introduction of an inert gas such as argon or any noble gas can be used into the chamber to stabilize the plasma (col.10, lines 66-col.11, lines 4).

Therefore, it would have been obvious to one skilled in the art at the time of claimed invention to employ Leiphart's teaching into modified Kawasaki's method for stabilizing the plasma as taught by Leiphart.

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Allowable Subject Matter

7. Claims 31-32 are allowable over prior art.

8. The following is a statement of reasons for the indication of allowable subject matter: The prior art does not teach providing a chamber in which a portion is separated from a main part of the chamber by a deflectable member and also does not teach that the volume of the separated portion is larger than the main part as the context of claims 31 and 32.

Conclusion

9. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Hanawa (5,688,357) illustrates that plasma power is adjusted or varied to establish an accurate RF match instantly responsive to change in plasma impedance (abstract).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Shamim Ahmed Primary Examiner Art Unit 1765

SA February 16, 2007